

2SK2179

(F3E50VX2)

500V 3A

FEATURES

- Input capacitance (Ciss) is small.
Especially, input capacitance at 0 bias is small.
- The static Rds(on) is small.
- The switching time is fast.

APPLICATION

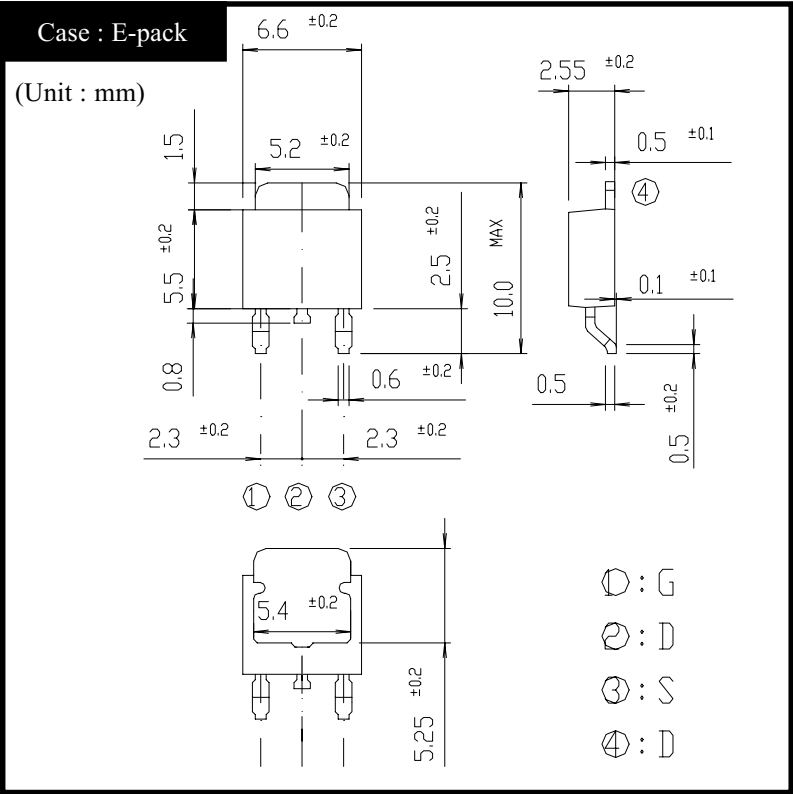
- Switching power supply of AC 100V input
- High voltage power supply
- Inverter

RATINGS

●Absolute Maximum Ratings (Tc = 25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-55~150	°C
Channel Temperature	T _{ch}		150	
Drain-Source Voltage	V _{DSS}		500	V
Gate-Source Voltage	V _{GSS}		±30	
Continuous Drain Current (DC)	I _D		3	A
Continuous Drain Current (Peak)	I _{DP}		9	
Continuous Source Current (DC)	I _S		3	
Total Power Dissipation	P _T		20	W
Single Pulse Avalanche Current	I _{AS}	T _{ch} = 25°C	3	A

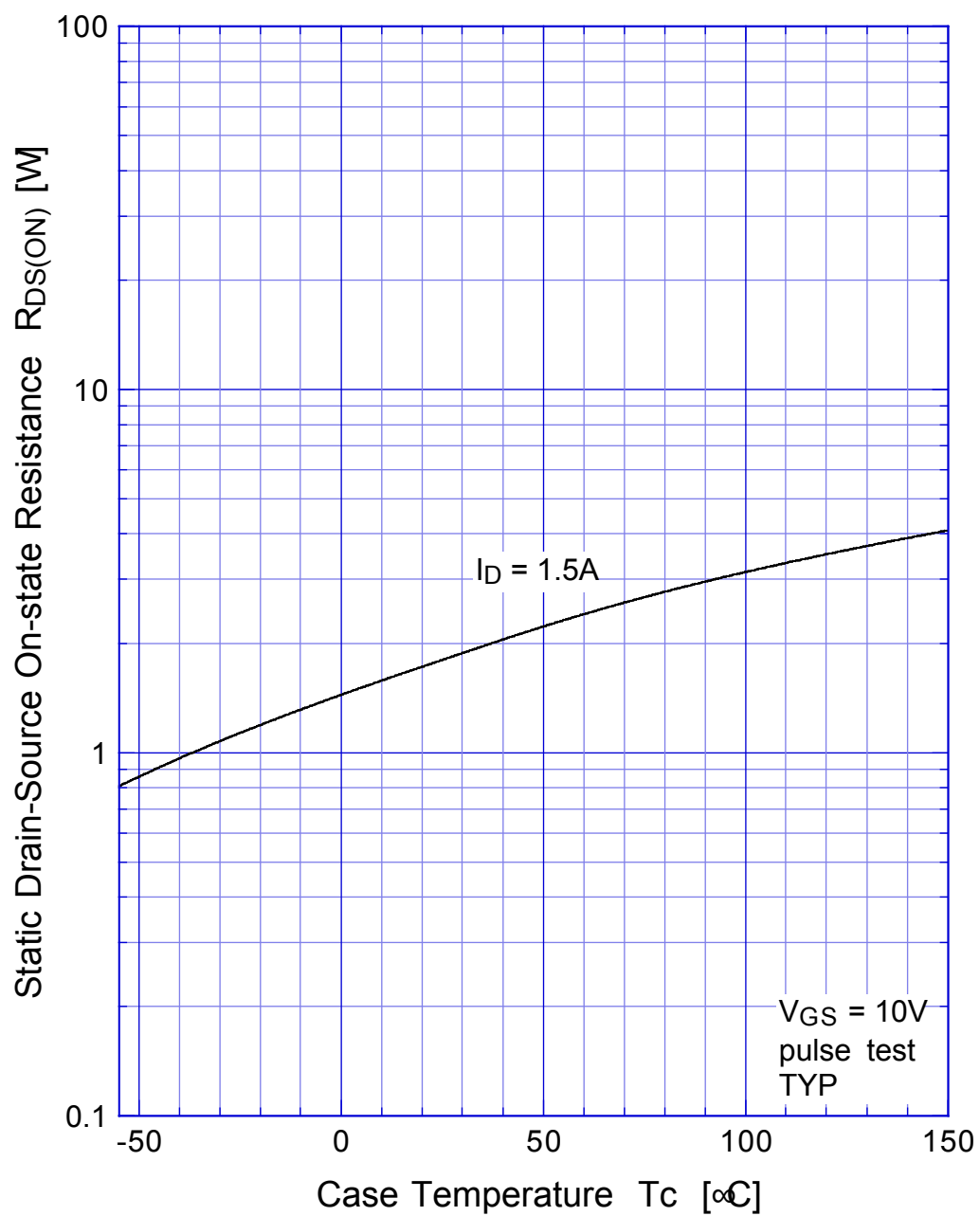
OUTLINE DIMENSIONS



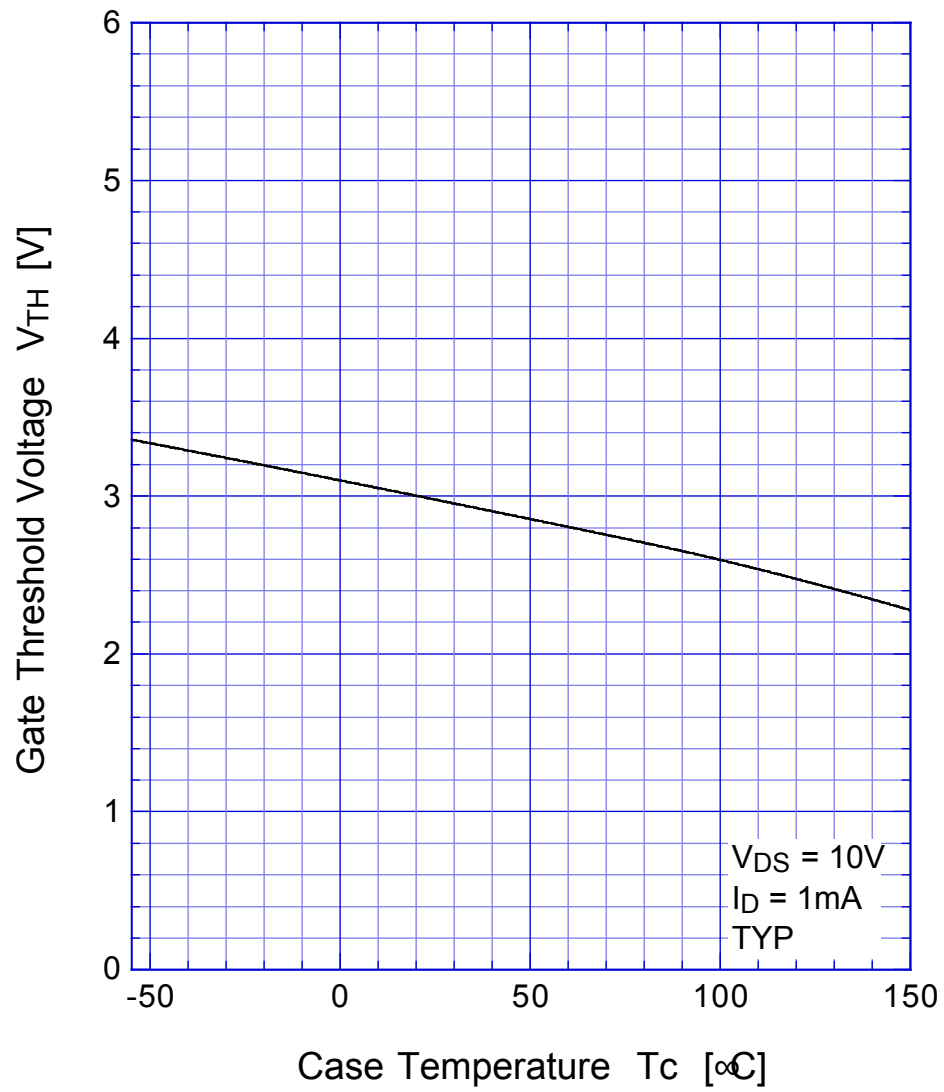
●Electrical Characteristics T_c = 25°C

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0V	500			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500V, V _{GS} = 0V			250	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V			±0.1	
Forward Transconductance	g _{fs}	I _D = 1.5A, V _{DS} = 10V	0.9	2.1		S
Static Drain-Source On-state Resistance	R _{DS(ON)}	I _D = 1.5A, V _{GS} = 10V		1.8	2.3	Ω
Gate Threshold Voltage	V _{TH}	I _D = 0.3mA, V _{DS} = 10V	2.5	3.0	3.5	V
Source-Drain Diode Forwade Voltage	V _{SD}	I _S = 1.5A, V _{GS} = 0V			1.5	
Thermal Resistance	θ _{jc}	junction to case			6.25	°C/W
Total Gate Charge	Q _g	V _{DD} = 400V, V _{GS} = 10V, I _D = 3A		15		nC
Input Capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz		400		pF
Reverse Transfer Capacitance	C _{rss}			30		
Output Capacitance	C _{oss}			90		
Turn-On Time	t _{on}	I _D = 1.5A, V _{GS} = 10V, R _L = 100Ω		45	80	ns
Turn-Off Time	t _{off}			90	140	

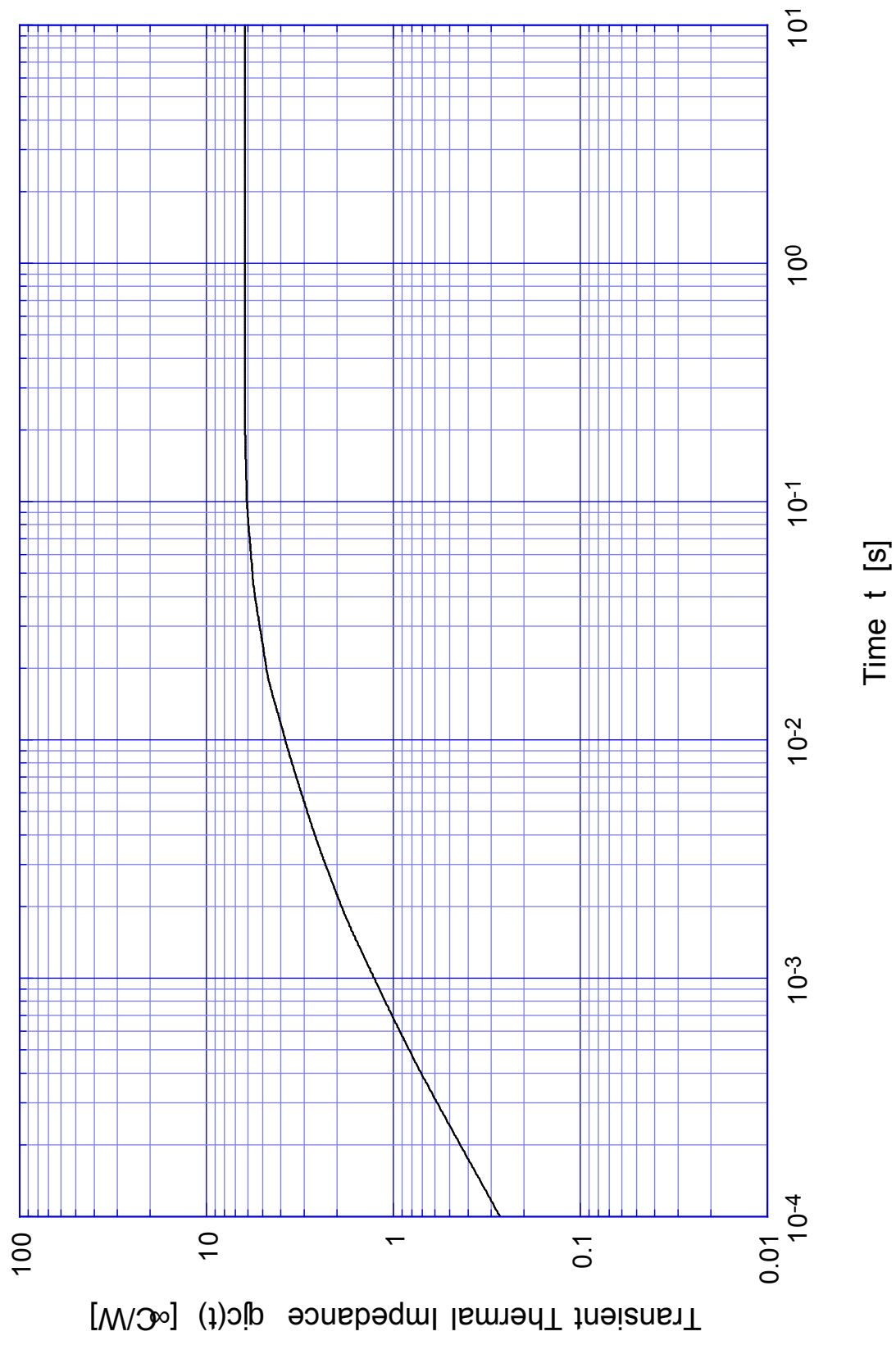
2SK2179 Static Drain-Source On-state Resistance



2SK2179 Gate Threshold Voltage



2SK2179 Transient Thermal Impedance



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Power Derating

